

# **QSI LASER DIODE**

## **SPECIFICATIONS FOR APPROVAL**

**Customer :**

**Model : QL80S4H-A/B/C/D/E-Y**

***Tentative***

### **Signature of Approval**

**Approved by** \_\_\_\_\_

**Checked by** \_\_\_\_\_

**Issued by** \_\_\_\_\_

### **Approval by Customer**



**QSI Co., Ltd.**

**315-9, Chunheung-ri, Sungger-eup,  
Cheonan-city, Chungnam, Korea 330-836**

**WWW.QSILaser.com**

*Tentative*

# QL80S4H-A/B/C/D/E-Y

## Laser Diode

Quantum Semiconductor International Co., Ltd.

Ver.4 July. 2005

### ◆ OVERVIEW

QL80S4H-A/B/C/D/E-Y is a MOCVD grown 808nm band laser diode with quantum well structure. It's an attractive light source, with a typical light output power of 500mW for optoelectronic devices such as solid state laser pumping and medical use.

### ◆ APPLICATION

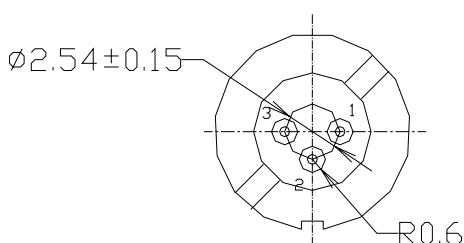
- Solid state laser excitation
- Medical use
- Material processes
- Measurement

### ◆ FEATURES

- Optical Power Output : 500mW CW
- Package Type : TO-5 (9mmφ)
- Polarization Mode : TM Mode (Type Y)
- Built-in Photo Diode for Monitoring Laser Diode (Option)

### ◆ ELECTRICAL CONNECTION

#### Bottom View



#### Pin Configuration

A	LD cathode, PD anode (Fig. 1)	QL80S4H-A
B	LD, PD anode (Fig. 2)	QL80S4H-B
C	LD anode, PD cathode (Fig. 3)	QL80S4H-C
D	LD cathode, No PD (Fig. 4)	QL80S4H-D
E	LD anode, No PD (Fig. 5)	QL80S4H-E

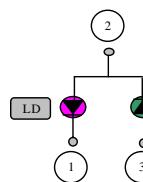


Fig. 1

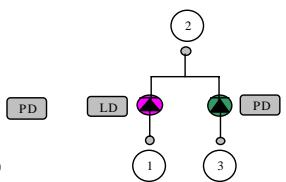


Fig. 2

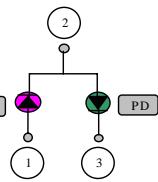


Fig. 3

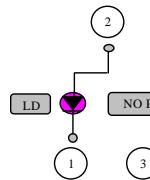


Fig. 4

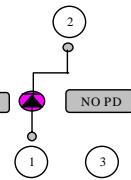


Fig. 5

*Tentative*

◆ ABSOLUTE MAXIMUM RATING at Tc=25°C

Items	Symbols	Values	Unit
Optical Output Power	P	500	mW
Laser Diode Reverse Voltage	V	2	V
Photo Diode Reverse Voltage	V	30	V
Operating Temperature	Topr	-10 ~ +40	°C
Storage Temperature	Tstg	-40 ~ +85	°C

◆ ELECTRICAL and OPTICAL CHARACTERISTICS at Tc=25°C <sup>1)2)</sup>

Items	Symbols	Min.	Typ.	Max.	Unit	Condition
Optical Output Power	Po	-	500	-	mW	-
Threshold Current	Ith	-	100	200	mA	-
Operating Current	Iop	-	550	700	mA	Po=500mW
Operating Voltage	Vop	-	2.2	3	V	Po=500mW
Lasing Wavelength	λp	803	808	813	nm	Po=500mW
Beam Divergence <sup>3)</sup>	θ	4	8	17	deg	Po=500mW
	θ ⊥	20	30	40	deg	Po=500mW
Beam Angle	Δθ	-	-	±3	deg	Po=500mW
	Δθ ⊥	-	-	±3	deg	Po=500mW
Monitor Current	Im	-	-	-	mA	
Polarization					TM mode	
Optical Distance	ΔX, ΔY, ΔZ	-	-	±80	μm	-

1) Initial values      2) All above values are evaluated with QSI's measuring apparatus

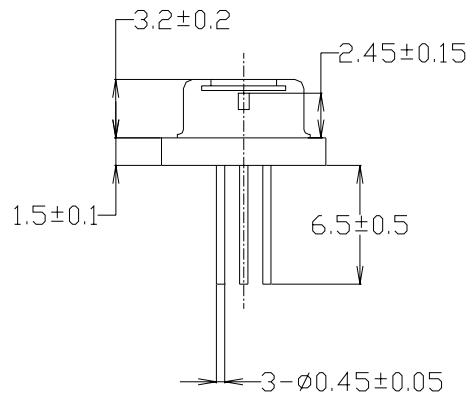
3) Full angle at half maximum

**NOTICE : QL80S4H-A/B/C/D/E-Y to be operated on APC circuit.**

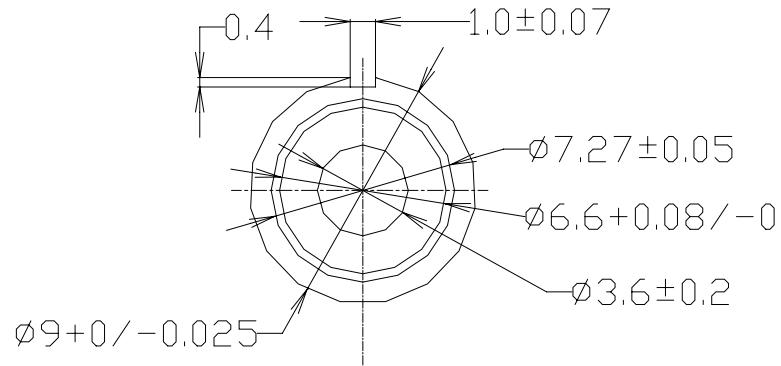
The above product specifications are subject to change without notice.



## PACKAGE DIMENSION



TOP VIEW



BOTTOM VIEW

